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# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T <sub>b</sub> =25°C)					電気的特性 (T <sub>b</sub> =25°C)										備考	
				V <sub>ceo</sub> (V)	V <sub>ceo</sub> (V)	I <sub>c</sub> (mA)	P <sub>c</sub> (mW)	T <sub>j</sub> (°C)	I <sub>ceo</sub> 最大値 (μA)	直流又はパルスI <sub>BE</sub>		バイアス		h <sub>FE</sub>	h <sub>FE</sub> h <sub>FE</sub> * (Ω)	h <sub>FE</sub> h <sub>FE</sub> * (×10 <sup>-4</sup> )	h <sub>FE</sub> h <sub>FE</sub> * (μS)	f <sub>αB</sub> f <sub>r</sub> * (Mc)		C <sub>ob</sub> (pF)
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I<sub>CBO</sub> MAXIMUM VALUE AND V<sub>CB</sub> VALUE (CRITERIA FOR MEASURING I<sub>CBO</sub>)
- 7 STANDARD VALUE OF DC/PULSE h<sub>FE</sub> AND V<sub>CE</sub>, I<sub>C</sub> (CRITERIA FOR MEASURING DC/PULSE h<sub>FE</sub>)
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V<sub>CB</sub>, I<sub>E</sub> (CRITERIA FOR MEASURING h PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
  - 9 f<sub>αB</sub> OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF f<sub>r</sub>.
  - 10 C<sub>ob</sub> AND r<sub>bb'</sub> OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN r<sub>bb'</sub> COLUMN WHICH INDICATES VALUE OF h<sub>ie</sub> (real)
  - 11 OUTLINE
  - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 ( $T_a = 25^\circ\text{C}$ )					電 気 的 特 性 ( $T_a = 25^\circ\text{C}$ )											外 形	備 考					
				$V_{CB0}$	$V_{EBO}$	$I_C$	$P_C$	$T_j$	$I_{CB0}$ 最大値		直 流 又 は バ ル ス $h_{FE}$				バ イ ア			$h_{fe}$	$h_{ie}$			$h_{re}$	$h_{oe}$	$f_{ab}$	$C_{ob}$	$r_{bb}$
				(V)	(V)	(mA)	(mW)	( $^\circ\text{C}$ )	( $\mu\text{A}$ )	$V_{CB}(V)$	$V_{CE}(V)$	$I_C(mA)$	$V_{CB}(V)$	$I_E(mA)$	$h_{fb}^*$	$h_{ie}$ ( $\Omega$ )	$h_{re}^*$ ( $\times 10^{-4}$ )	$h_{ob}^*$ ( $\mu\text{U}$ )	$f_{ab}$ $f_T^*$ (Mc)			(pF)	$r_{bb}$ $r_{ie}(real)^*$ ( $\Omega$ )			
2SD206	新電元	PA. SW	Si. DJ	50	8	10A	150W ( $T_c=25^\circ\text{C}$ )	150	50mA	30	20	5	5 A	10	-1A	50	7	70	10m $\bar{C}$	$f_{oe}$ 18kc				102		
# 207	"	"	"	100	8	10A	150W ( $T_c=25^\circ\text{C}$ )	150	50mA	30	20	5	5 A	10	-1A	50	7	70	10m $\bar{C}$	$f_{oe}$ 18kc				102		
# 208	"	"	"	150	8	10A	150W ( $T_c=25^\circ\text{C}$ )	150	50mA	30	20	5	5 A	10	-1A	50	7	70	10m $\bar{C}$	$f_{oe}$ 18kc				102		
# 209																										
# 210																										
# 211	サンケン	PA. SW	Si. DJ	60	6	10A	100W ( $T_c=25^\circ\text{C}$ )	150	50	40	30	4	5 A	12	-500					8				102		
# 212	"	"	"	90	6	1 A	100W ( $T_c=25^\circ\text{C}$ )	150	50	40	30	4	5 A	12	-500					8				102		
# 213	"	"	"	110	6	10A	100W ( $T_c=25^\circ\text{C}$ )	150	50	40	30	4	5 A	12	-500					8				102		
# 214	"	"	"	130	6	10A	100W ( $T_c=25^\circ\text{C}$ )	150	50	40	30	4	5 A	12	-500					8				102		
# 215	富士通	PA	"	40	5	1 A	800	175	20	30	70	4	500	4	-100					1.2				84B		
# 216	"	"	"	60	5	1 A	800	175	20	30	70	4	500	4	-100					1.2				84B		
★ # 217	日電	"	Si. EMe	120	7	7 A	60W ( $T_c=25^\circ\text{C}$ )	150	500	80	60	5	4 A	10	-200					10*				102	2SA648 とコンプリ	
# 218	"	"	"	150	7	7 A	60W ( $T_c=25^\circ\text{C}$ )	150	500	80	60	5	4 A	10	-200					10*				102	2SA649 とコンプリ	
# 219	サンケン	PA. SW	Si. DJ	40	6	1 A	500	150	1	20	80	4	200	5	-100					8				84B		
# 220	"	"	"	80	6	1 A	500	150	1	20	80	4	200	5	-100					8				84B		
# 221	"	"	"	110	6	1 A	500	150	1	20	80	4	200	5	-100					8				84B		
★ # 222	"	"	"	40	7	1.5 A	10W ( $T_c=25^\circ\text{C}$ )	150	10	20	80	4	500	5	-100					8				97B		
★ # 223	"	"	"	80	7	1.5 A	10W ( $T_c=25^\circ\text{C}$ )	150	10	20	60	4	500	5	-100					8				97B		
★ # 224	"	"	"	110	7	1.5 A	10W ( $T_c=25^\circ\text{C}$ )	150	10	20	40	4	500	5	-100					8				97B		
# 225																										
★ # 226	松下	PA	Si. DJ	40	8	3 A	25W ( $T_c=25^\circ\text{C}$ )	150	30	20	50	3	1 A	10	-200					$f_{oe}$ 25kHz				99		
★ # 227	日電	"	Si. E	30	5	300	250	125	0.1	15	150	1	50											138	2SA642 とコンプリ	
★ # 228	"	"	"	30		300	400	125	0.1	15	120	1	300	10	-10	200								44		
# 229																										
# 230																										
# 231	富士通	SW. AF	Si. TMe	50	5	30A	125W ( $T_c=25^\circ\text{C}$ )	175	100	30	25	4	10 A											102		
# 232	"	"	"	120	7	30A	125W ( $T_c=25^\circ\text{C}$ )	175	1 mA	50	25	4	10 A											102		
# 233																										
# 234	東芝	PA	Si. T	60	10	3 A	25W ( $T_c=25^\circ\text{C}$ )	150	100	20	40-240	5	500	10	-500					3*	90		268	2SB434 とコンプリ		
# 235	"	"	"	50	10	3 A	25W ( $T_c=25^\circ\text{C}$ )	150	100	20	40-240	5	500	10	-500					3*	90		268	2SB435 とコンプリ		